

<p style="text-align: center;"> U.S. PATENT AND TRADEMARK OFFICE FORM PTO-1449 (MODIFIED) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT </p>	ATTORNEY DOCKET NO.	
	SP03-165	
	10/718,744	
	APPLICANT Rajaram Bhat, et al.	
FILING DATE November 21, 2003	GROUP: 1762	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date if Approp.
SP	AA	5,209,952	5/11/93	Erdmann et al	427	255.6	

FOREIGN PATENT DOCUMENTS

CONTINUATION DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation Yes No
CD	AB	WO03/041137	5/15/03	PCT	H01L	21/20	X
	AB	EP1061083	12/20/00	Europe	C07F	5/00	X
	AD	EP1361606	11/12/03	Europe	H01L	21/36	X

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	AE	Kurtz, et al.; "Incorporation of nitrogen into GaAsN grown by MOCVD using different precursors"; Journal of Crystal Growth 234 (2002) pgs 318-322.
	AF	Devi, et al.; "A Study of Bisazido (dimethylaminopropyl) gallium as a Precursor for the OMVPE of Gallium Nitride Thin Films in a Cold-Wall Reactor System under Reduced Pressure"; Chemical Vapor Deposition 2000, 6, No. 5, pgs 245-252.

EXAMINER

DATE CONSIDERED:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (MODIFIED)		ATTORNEY DOCKET NO.	SERIAL NO.
<p style="text-align: center;">LIST OF PATENTS AND PUBLICATIONS FOR APPLICANTS INFORMATION DISCLOSURE STATEMENT</p>		SP03-165	
		APPLICANT RAJARAM BHAT, et al.	
		FILING DATE	GROUP:

REFERENCE DESIGNATION		U.S. PATENT and PUBLICATION DOCUMENTS					
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date if Approp.
<i>ef</i>	AA	2002/0085973A1	7/4/02	Park	423	351	
	AB	5,689,123	11/18/97	Major, et al	257	190	
	AC	5,891,790	4/6/99	Keller, et al	438	508	
	AD	5,944,913	8/31/99	Hou	136	255	
	AE	6,046,096	4/4/00	Ouchi	438	510	
	AF	6,252,287	6/26/01	Kurtz, et al	257	461	
	AG	6,342,405	1/29/02	Major, et al	438	46	
	AH	6,358,822	3/19/02	Tomomura	438	483	
	AI	6,596,079	7/22/03	Vaudo, et al	117	97	
<i>ef</i>	AJ	6,645,885	11/11/03	Chua, et al	438	962	
	AK						

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation Yes No
		AL					

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>ef</i>	AM	"Room Temperature Operation of GaInNAs/GaInP Double-Heterostructure Laser Diodes Grown by Metalorganic Chemical Vapor Deposition", Sato, et al Jpn. J. Appl. Phys. Vo. 36 1997 pp 2671-2675
	AN	"Incorporation effects in MOCVD-grown (IN)GaAsN using different nitrogen precursors", Ptak, et al J. of Crystal Growth Vol. 243 (2002) 231-237
	AO	"Red Shift of Photoluminescence and Absorption in Dilute GaAsN Alloy Layers", Weyers, et al Jpn. J. Appl. Phys. Vo. 31 1992 pp L853-L855
	AP	"GaInNAs: A Novel Material for Long-Wavelength-Range Laser Diodes with Excellent high-Temperature Performance", Kondow, et al Jpn. J. Appl. Phys. Vo. 35 199 pp 1273-1275
	AQ	"Gas-Source Molecular Beam Epitaxy of GaN _x As _{1-x} Using a N Radical as the N Source", Konkow, et al Jpn. J. Appl. Phys. Vo. 3 1994 pp L1056-L1058
	AR	"Structural characterization of a dimeric dimethylindium azide and its use as a single-source precursor for InN thin films", Bae, et al J. of Organic Metallic Chemistry 616(2000) 128-134
<i>ef</i>	AS	"Preparation of Phase-Pure InSe Thin Films by MOCVD Using a New Single-Source Precursor [(Me) ₂ In(μ-SeMe)] ₂ ", Cho, et al Bull. Korean Chem. Soc. 2003 Vol. 24, No. 5 645-646

EXAMINER: *[Signature]* DATE CONSIDERED: *5/5/05*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.